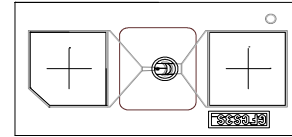


## Solderable GaAs Flip Chip Schottky Diode

Rev. V3

### Features

- Usable Past 80GHz
- Low Series Resistance
- Low Capacitance
- High Cutoff Frequency
- Silicon Nitride Passivation
- Polyimide Scratch Protection
- Lead Free (RoHS Compliant)
- Designed for Easy Circuit Insertion
- Available in Pocket Tape and Reel
- **Can be Mounted with Solder or Conductive Epoxy**



**MADS-001317- 1500**

### Description and Applications

M/A-COM's MADS-001317-1500 single is a gallium arsenide flip chip Schottky barrier diode. This device is fabricated on OMCVD epitaxial material using a process designed for high device uniformity and extremely low parasitics. This diode is fully passivated with silicon nitride and has an additional layer of polyimide for scratch protection. The protective coating prevents damage to the junction during automated or manual handling. The flip chip configuration is suitable for pick and place insertion. This device can be attached with solder or conductive epoxy. The high cutoff frequency of this diode allows use through millimeter wave frequencies. Typical applications include single and double balanced mixers in PCN transceivers and radios, police radar detectors, and automotive radar detectors.

### Ordering Information

Part Number	Package
MADS-001317-1500AG	Gel Pack
MADS-001317-1500AP	Pocket Tape and Reel

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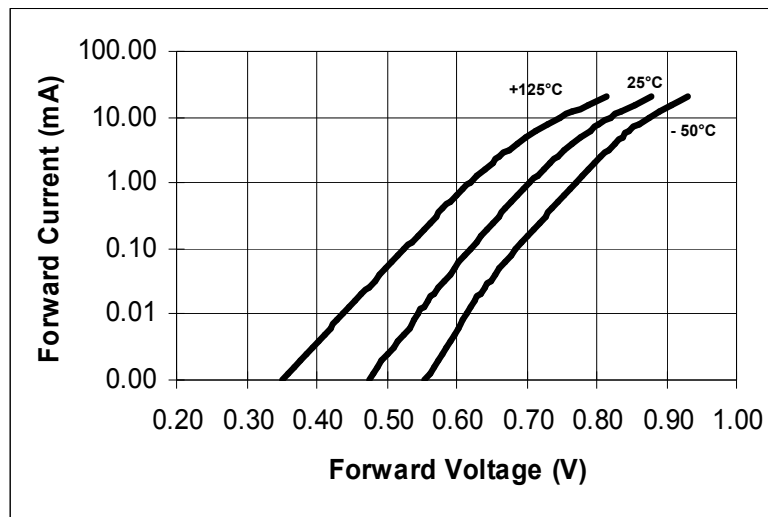
### Electrical Specifications @ + 25 °C

Parameters and Test Conditions	Symbol	Units	MADS-001317-1500		
			Min.	Typ.	Max.
Junction Capacitance at 0V at 1 MHz	Cj	pF		.020	
Total Capacitance at 0V at 1 MHz <sup>1</sup>	Ct	pF	.030	.045	.060
Dynamic Resistance at 9.5 - 10.5mA	Rs	Ohms		4	7
Forward Voltage at +1mA	Vf1	Volts	.60	.70	.80
Reverse Breakdown Voltage at -10uA	Vbr	Volts	4.5	7	

#### Notes:

1. Total capacitance is equivalent to the sum of junction capacitance Cj and parasitic capacitance Cp.

### Forward Current vs Temperature



### Absolute Maximum Ratings <sup>1</sup>

Parameter	Absolute Maximum
Operating Temperature	-65 °C to +125 °C
Storage Temperature	-65 °C to +150 °C
Incident LO Power	+20 dBm
Incident RF Power	+20 dBm .
Mounting Temperature	+260 °C
Electrostatic Discharge ( ESD ) Classification <sup>2</sup>	Class 0

1. Operation of this device above any one of these parameters may cause permanent damage.
2. Human Body Model

## Solderable GaAs Flip Chip Schottky Diode

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### Mounting Techniques

Die attach for these devices is made simple through the use of surface mount die attach technology. This chip was designed to be inserted onto hard or soft substrates with the junction side down. This chip can be mounted with conductive epoxy or with solder.

### Solder Die Attach:

This device can be mounted with Sn63/Pb37 or RoHS compliant solder. Typical reflow profiles are provided on M/A-Com application note M538, "Surface Mounting Instructions" which can be found @ [www.macomtech.com](http://www.macomtech.com)

### Epoxy Die Attach:

This device can also be attached with conductive epoxy. The assembly can be preheated to 125 - 150°C. Use a minimum amount of epoxy. Cure epoxy as per manufacturer's instructions.

### Handling Procedures

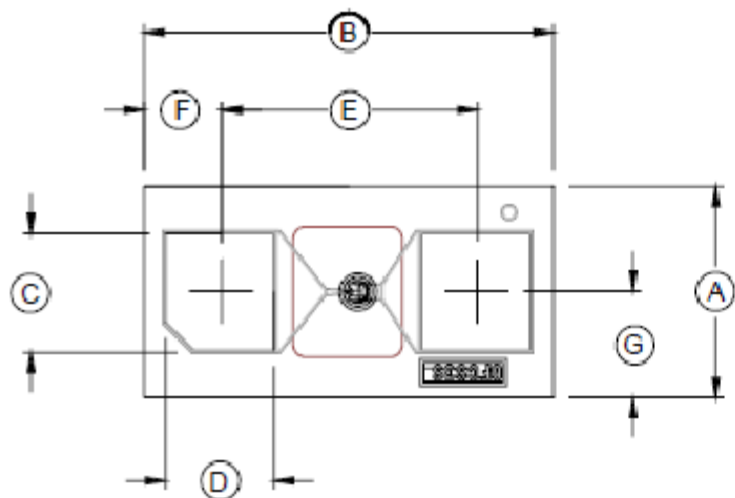
The following precautions should be observed to avoid damaging these chips:

- Cleanliness:** The chips should be handled in a clean environment. Do not attempt to clean die after installation.
- Static Sensitivity:** Schottky barrier diodes are ESD sensitive and can be damaged by static electricity. Proper ESD techniques should be used when handling these devices.
- General Handling:** The protective polymer coating on the active areas of these die provides scratch protection, particularly for the metal air bridge which contacts the anode. Die can be handled with tweezers or vacuum pickups and are suitable for use with automatic pick-and-place equipment.

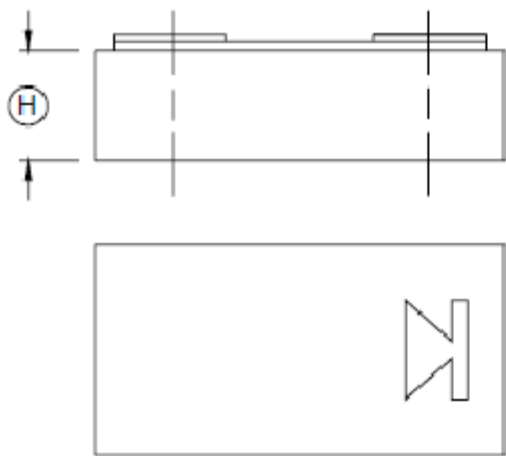
## Solderable GaAs Flip Chip Schottky Diode

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### Flip Chip Outline Drawing



Case Style 1500



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.015	0.017	0.381	0.431
B	0.029	0.031	0.736	0.787
C	0.008	0.009	0.203	0.228
D	0.007	0.008	0.178	0.203
E	0.016	0.017	0.406	0.431
F	0.006	0.007	0.152	0.178
G	0.0075	0.0085	0.190	0.216
H	0.0075	0.0085	0.190	0.216

1. Pad finish is .2 microns of gold over 4 microns of nickel.

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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